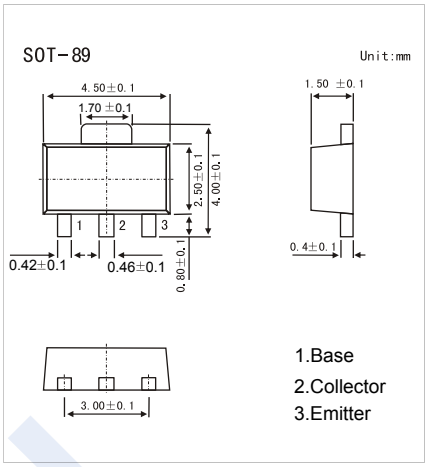
NPN Transistors

2SC4672



■ Features

- Low Saturation Voltage
- Excellent h_{FE} Characteristics
- Complementary to 2SA1797

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	60	V
Collector - Emitter Voltage	V_{CEO}	50	
Emitter - Base Voltage	V_{EBO}	6	
Collector Current - Continuous	I_C	2	A
Collector Power Dissipation	P_C	500	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	250	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= 50 μA, I_E= 0	60			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= 1 mA, I_B= 0	50			
Emitter - base breakdown voltage	V_{EBO}	I_E= 50 μ A, I_C= 0	6			
Collector-base cut-off current	I_{CBO}	V_{CB}= 60V , I_E= 0			0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= 5V , I_C=0			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=1A, I_B=50mA			0.35	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=1A, I_B=50mA			1.2	
DC current gain	h_{FE}	V_{CE}= 2V, I_C= 500mA	82		390	
Collector output capacitance	C_{ob}	V_{CB}= 10V, I_E= 0,f=1MHz		25		pF
Transition frequency	f_T	V_{CE}= 2V, I_C= 500mA,f=100MHz		210		MHz

■ Classification of hfe

Type	2SC4672-P	2SC4672-Q	2SC4672-R
Range	82-180	120-270	180-390
Marking	DKP	DKQ	DKR

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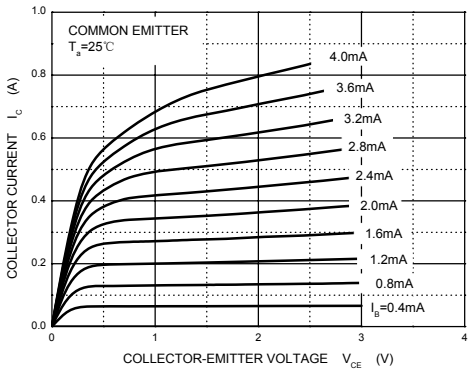
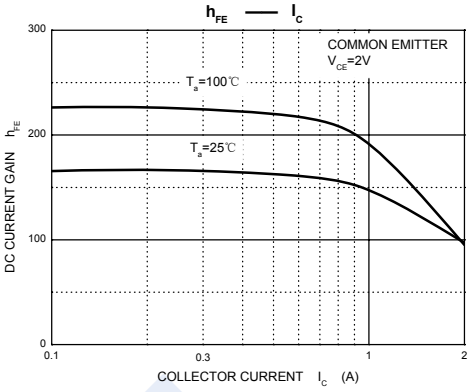
■ Typical Characterisitics

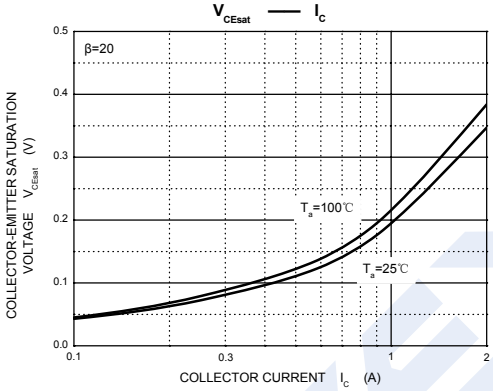
Static Characteristic



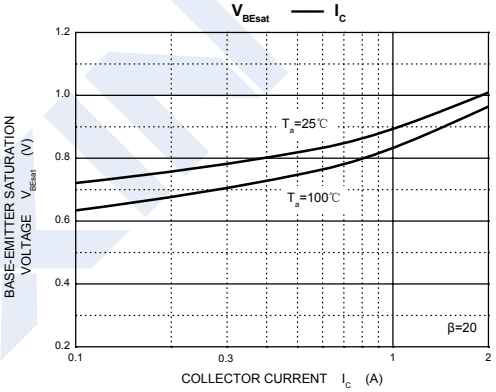
hFE — IC



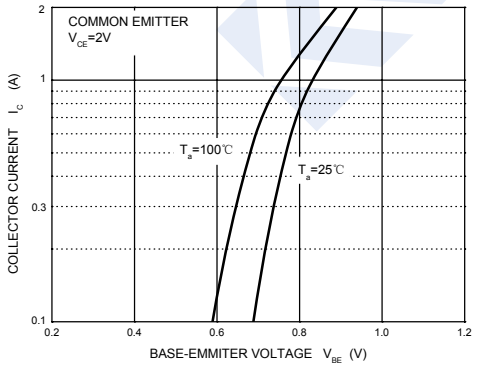
VCEsat — IC



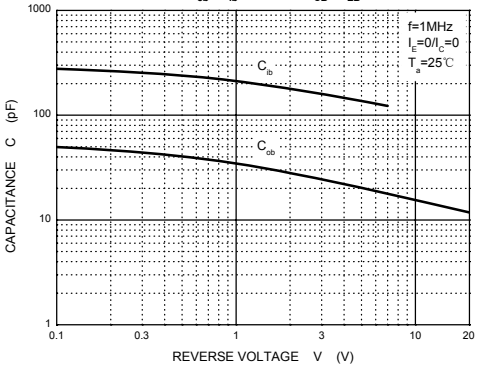
VBEsat — IC



IC — VBE



Cob/ Cib — VCB/ VEB



PC — Ta